MSKSEMI















ESD

TVS

TSS

MOV

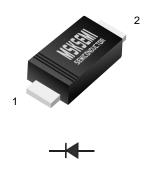
GDT

PLED

Broduct data sheet

F1A THRU F1M HF





SOD-123FL

FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Fast switching speed

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25°C ambient temperature unless otherwies specified. Single phase half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

TYPE NUMBER	F1A	F1B	F1D	F1G	F1J	F1K	F1M	UNITS
Maximum Recurrent Peak Reverse Voltage		100	200	400	600	800	1000	V
Maximum RMS Voltage		70	140	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current								
at Ta=25°C		1.0			Α			
Peak Forward Surge Current, 8.3 ms single half sine-wave								
superimposed on rated load (JEDEC method)		30					Α	
Maximum Instantaneous Forward Voltage at 1.0A		1.3						V
Maximum DC Reverse Current Ta=25°C		5.0			μА			
at Rated DC Blocking Voltage Ta=100°C		100			μА			
Maximum Reverse Recovery Time (Note 1)		150		250	50	00	nS	
Typical Junction Capacitance (Note 2)	15			pF				
Typical Thermal Resistance R JA (Note 3)	80			°C/W				
Operating and Storage Temperature Range Тл, Тsтв	-65 — +150			°C				
Marking Code								

- 1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
- 3. Thermal Resistance from Junction to Ambient.





FIG.1-TYPICAL FORWARD

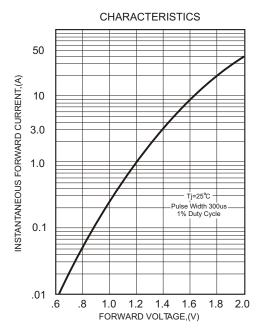
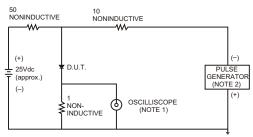


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF

2. Rise Time= 10ns max., Source Impedance= 50 ohms.

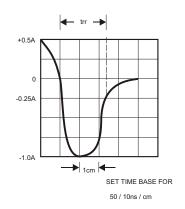


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

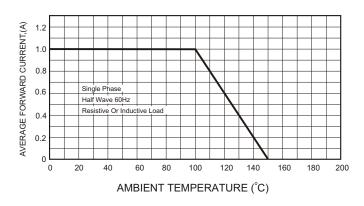


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

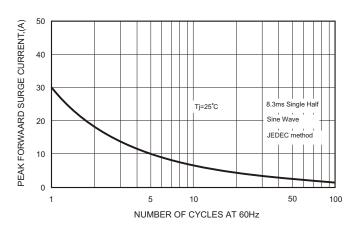
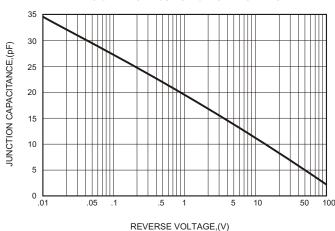
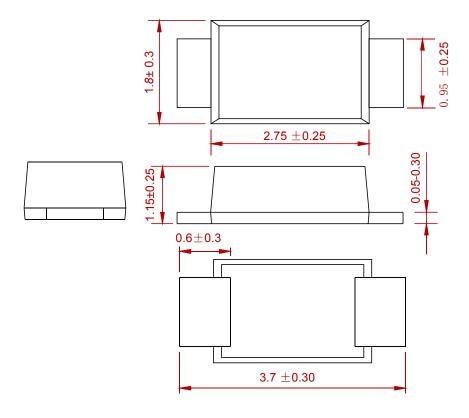


FIG.5-TYPICAL JUNCTION CAPACITANCE

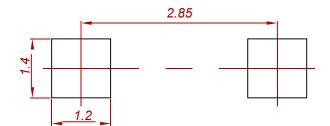


PACKAGE MECHANICAL DATA



Dimensions in millimeters

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
F1A THRU F1M	SOD-123FL	3000



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